

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max $T_A = +25^\circ\text{C}$
20V	72m Ω @ $V_{GS} = 4.5\text{V}$	3.4A
	110m Ω @ $V_{GS} = 2.5\text{V}$	2.7A

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

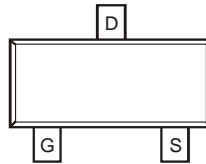
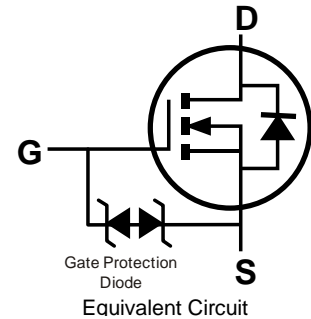
- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors



SOT23



Top View


 Top View
Pin Configuration

 Gate Protection
Diode
Equivalent Circuit

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD protected gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

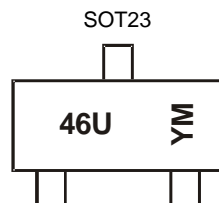
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2046U-7	SOT23	3,000/Tape & Reel
DMN2046U-13	SOT23	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



46U = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: B = 2014)
 M = Month (ex: 9 = September)

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020	2021
Code	B	C	D	E	F	G	H	I

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C	I _D	3.4	A
		T _A = +70°C		2.7	
Pulsed Drain Current (Pulse width ≤10μS, Duty Cycle ≤1%)			I _{DM}	18	A

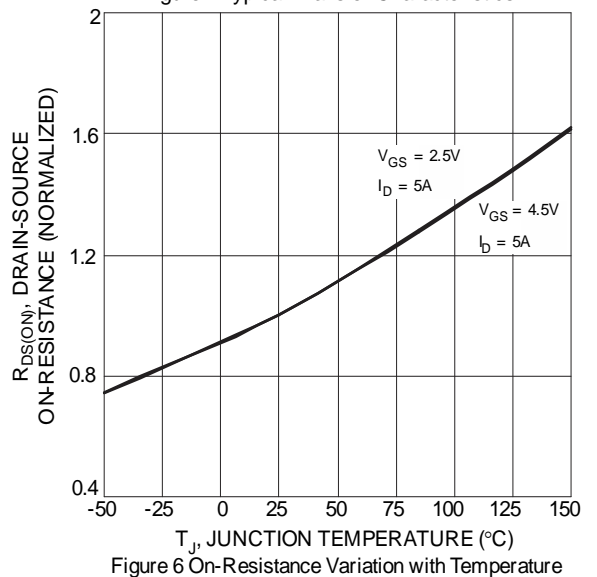
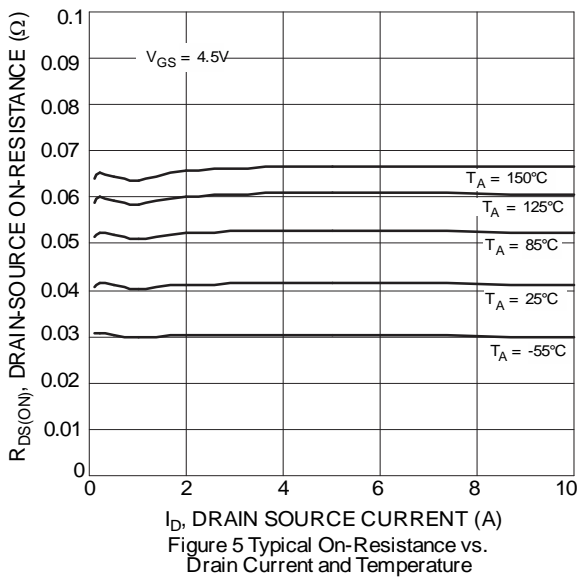
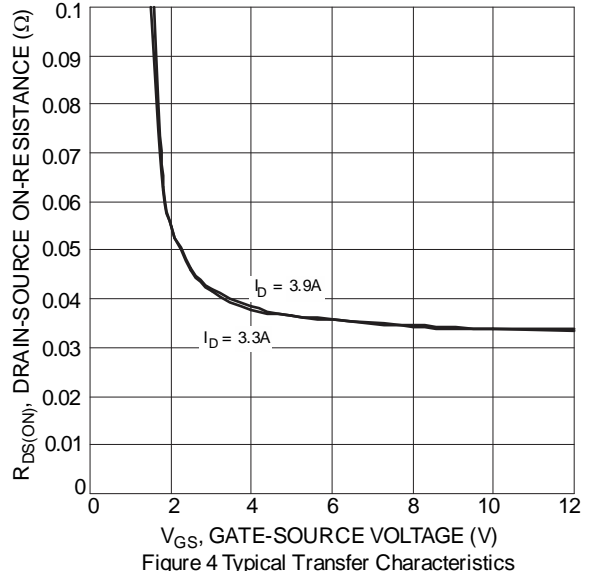
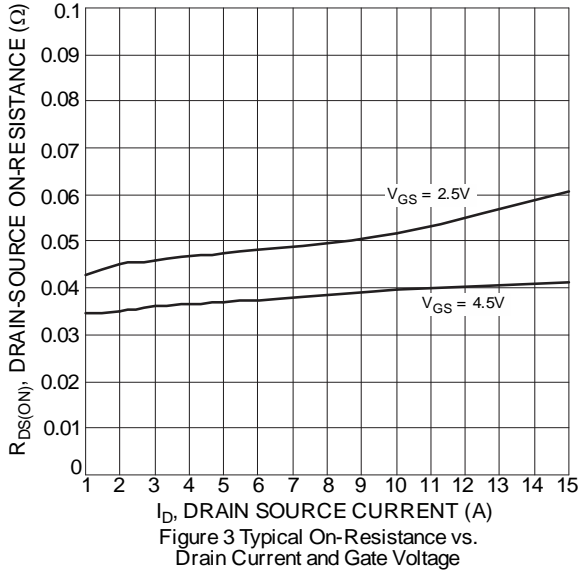
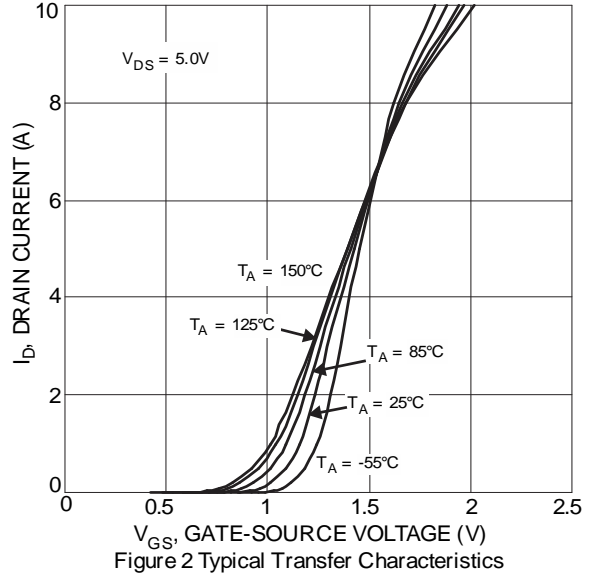
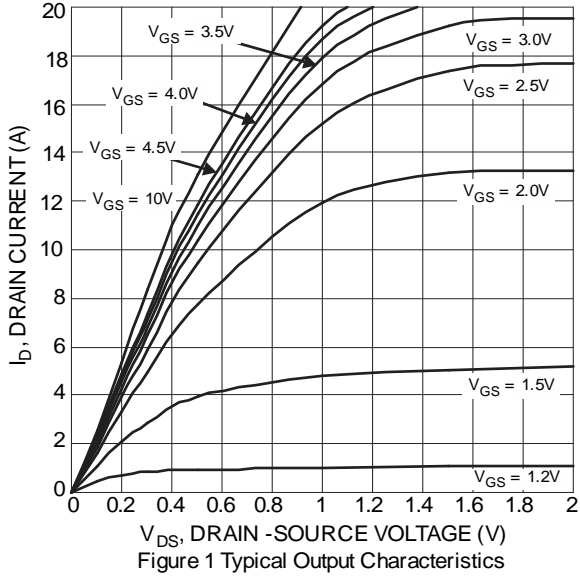
Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	0.76	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	166	°C/W
Power Dissipation (Note 6)	P _D	1.26	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	100	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = +25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	-	1.0	μA	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±10	μA	V _{GS} = ±10V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	0.4	-	1.4	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	-	72	mΩ	V _{GS} = 4.5V, I _D = 3.6A
				110		V _{GS} = 2.5V, I _D = 3.1A
Diode Forward Voltage	V _{SD}	-	-	1.2	V	V _{GS} = 0V, I _S = 0.94A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iSS}	-	292	-	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	36	-	pF	
Reverse Transfer Capacitance	C _{rSS}	-	32	-	pF	
Gate Resistance	R _g	-	63	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	-	3.8	-	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 5.1A
Gate-Source Charge	Q _{gs}	-	0.5	-	nC	
Gate-Drain Charge	Q _{gd}	-	0.8	-	nC	
Turn-On Delay Time	t _{D(on)}	-	6.7	-	ns	V _{DD} = 10V, V _{GS} = 4.5V, R _L = 2.4Ω, R _G = 6Ω
Turn-On Rise Time	t _r	-	25.1	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	69.1	-	ns	
Turn-Off Fall Time	t _f	-	34.1	-	ns	
Reverse Recovery Time	t _{rr}	-	18.2	-	ns	I _F = 4.1A, di/dt = 100A/μs
Reverse Recovery Charge	Q _{rr}	-	3.6	-	nC	I _F = 4.1A, di/dt = 100A/μs

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.



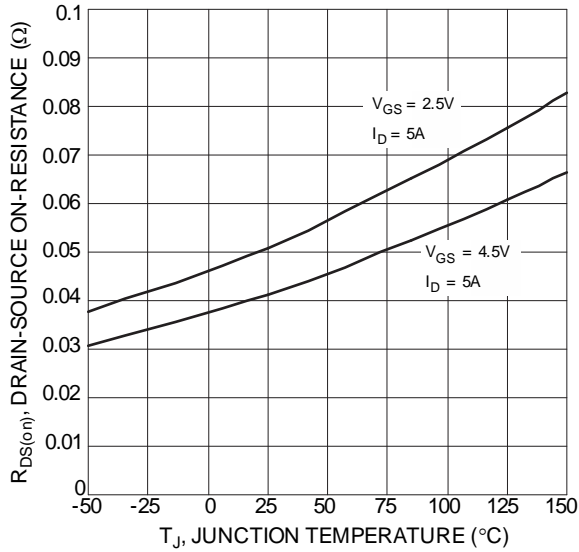


Figure 7 On-Resistance Variation with Temperature

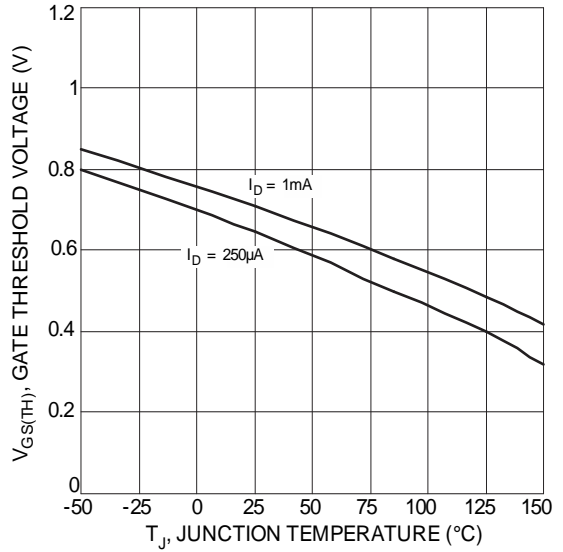


Figure 8 Gate Threshold Variation vs. Ambient Temperature

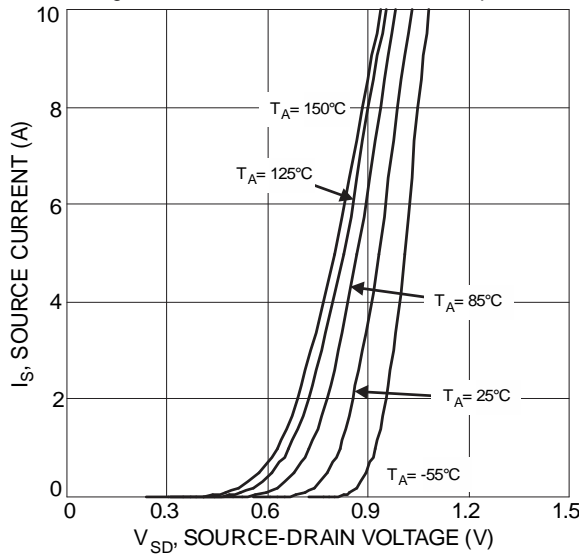


Figure 9 Diode Forward Voltage vs. Current

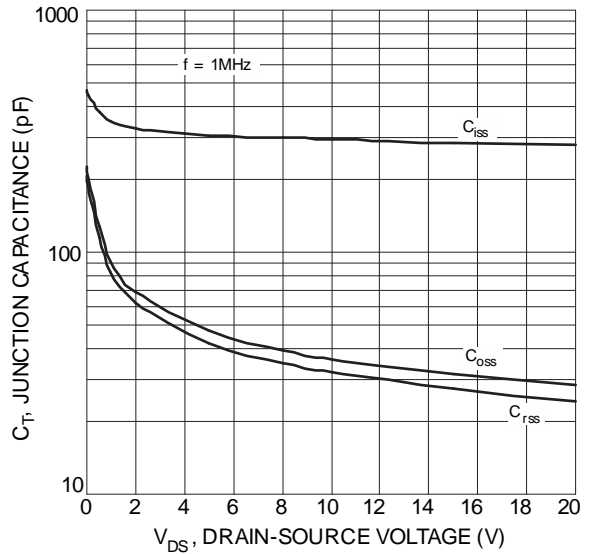


Figure 10 Typical Junction Capacitance

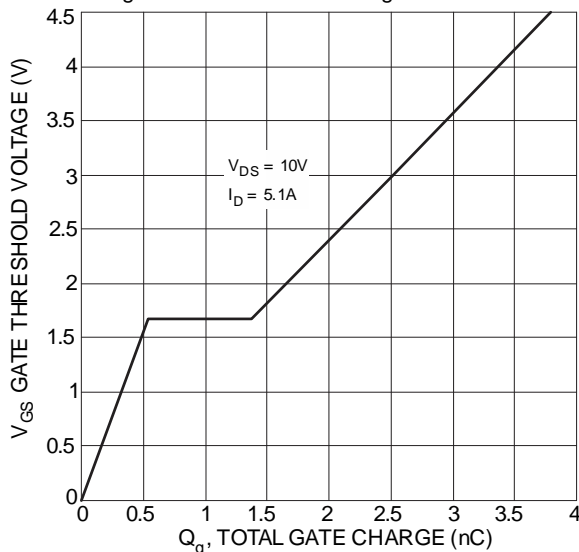


Figure 11 Gate Charge

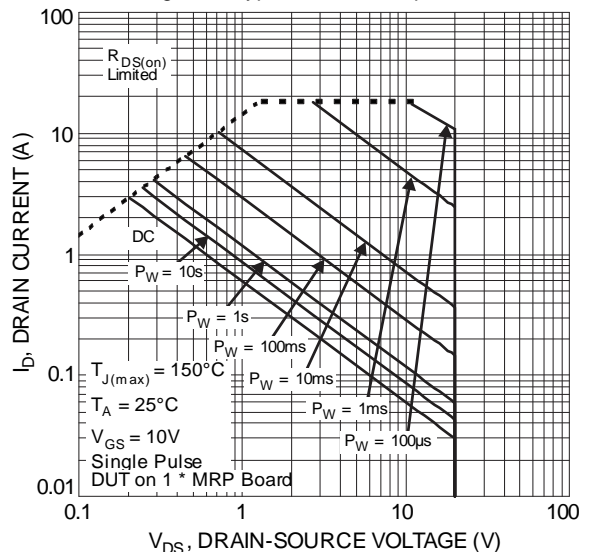
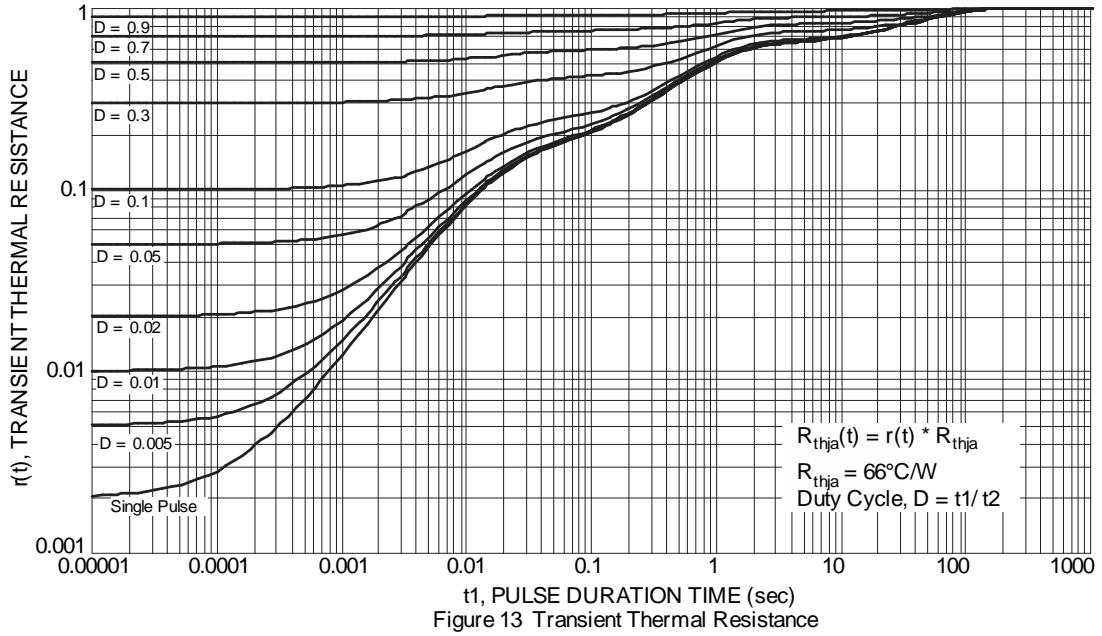
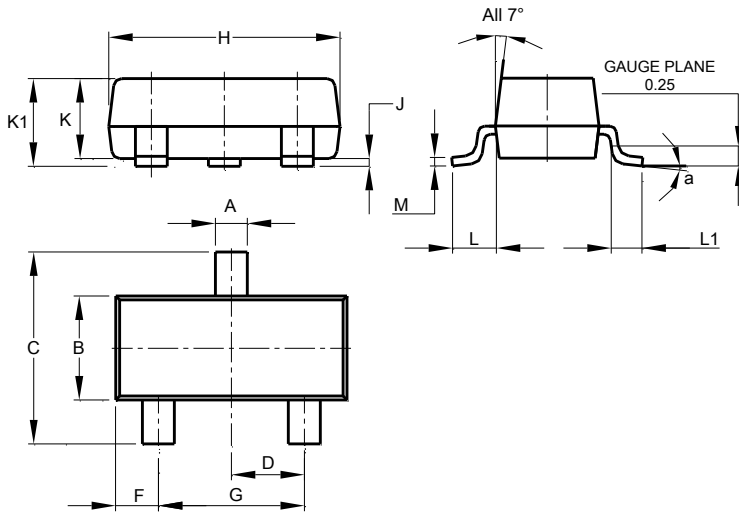


Figure 12 SOA, Safe Operation Area



Package Outline Dimensions

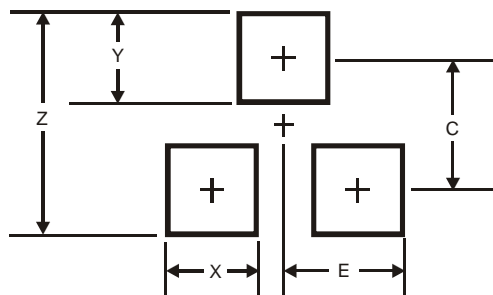
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	8°		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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